ABSTRACT OF THE DISCLOSURE

A solid state imaging device comprises channel regions of one conductivity type arranged to extend along a first direction in parallel to each other with predetermined intervals on one surface of a semiconductor substrate, drain regions of the one conductivity type at high doping density, which are arranged to extend along the first direction between adjacent channel regions, separation regions disposed in the interval between one of the channel regions and one of the drain regions, and transfer electrodes arranged in parallel to each other to extend along a second direction which intersects the first direction on the semiconductor substrate. The width of the separation region is narrower in a region beneath at least one transfer electrode in each predetermined set of transfer electrodes than in a region beneath the remaining transfer electrodes in the set of transfer electrodes.